

SOT-23 TRANSISTORS & DIODES

SCHOTTKY BARRIER DIODES

Type	V_{BR} at $I_R=10\mu A$ min. (Volts)	V_F at $I_F=1mA$ max. (mV)	I_R max. nA at V_R (volts)		I_F at $V_F=1V$ min. (mA)	C_T at $V_R=0V$ $f=1MHz$ max. (pF)
ZC2800E	70	410	200	50	15	2.0
*ZC2810E	20	410	100	15	35	1.2
ZC2811E	15	410	100	10	20	1.2
ZC5800E	50	410	200	35	15	2.0

*Not recommended for New Design - In (ZC2810E)

DUAL SCHOTTKY BARRIER DIODES

Type	V_{BR} at $I_R=10\mu A$ min. (Volts)	V_F at $I_F=1mA$ max. (mV)	I_R max. nA at V_R (volts)		I_F at $V_F=1V$ min. (mA)	C_T at $V_R=0V$ $f=1MHz$ max. (pF)	Pinning configuration
BAS70-04	70	410	200	50	15	2.0	Series
BAS70-05	70	410	200	50	15	2.0	Common cathode
BAS70-06	70	410	200	50	15	2.0	Common anode

SILICON ION IMPLANTED HYPERABRUPT TUNER DIODES

Type	Reverse breakdown Voltage V_R Volts max.	Nominal capacitance at $V_R=2V$, $f=1MHz$ C_{tot} pF			Capacitance ratio $f=1MHz$ C_2/C_{20}		Q at $V_R=3V$ $f=50MHz$ min.
		min.	typ.	max.	min.	max.	
ZC830A	25	9.0	10	11.0	4.5	6.0	300
ZC831A	25	13.5	15	16.5	4.5	6.0	300
ZC832A	25	19.8	22	24.2	5.0	6.5	200
ZC833A	25	29.7	33	36.3	5.0	6.5	200
ZC834A	25	42.3	47	51.7	5.0	6.5	200
ZC835A	25	61.2	68	74.8	5.0	6.5	100
ZC836A	25	90.0	100	110.0	5.0	6.5	100

Devices are also available with 5% and 20% tolerances. No suffix - $\pm 20\%$ (e.g. ZC830)
Suffix B - $\pm 5\%$ (e.g. ZC830B)

VARIABLE CAPACITANCE TUNER DIODES

Type	Reverse Breakdown Voltage V_R Volts	Nominal Capacitance at $f=1MHz$ C_{tot} pF				Capacitance ratio at $f=1MHz$ C_3/C_{25}			Q at $V_R=3V$ $f=50MHz$ Typ.
		Min.	Typ.	Max.	at V_R Volts	Min.	Typ.	Max.	
BBY31	28	1.8	—	2.8	25	—	5.0	—	—
BBY40	28	26	—	32	3	5	—	6.5	—
FMMV105G	30	4.3	—	6.0	25	—	—	—	—
FMMV109	30	1.8	—	2.8	25	4.0	—	6.0	350
FMMV3102	30	26	—	32	3	5.0	—	6.5	250
	30	26	—	25	3	4.5	—	—	300